MSKSEMI 美森科













FSD

TVS

TSS

MOV

GDT

PIFD

KTC3875

Product specification





FEATURES

- High hFE
- Low noise
- Complementary to KTA1504

Reference News



MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{СВО}	Collector-Base Voltage	60	V
Vceo	Collector-Emitter Voltage	50	٧
V _{EBO}	Emitter-Base Voltage	5	V
lc	Collector Current	150	mA
Pc	Collector Power Dissipation	150	mW
Roja	Thermal Resistance From Junction To Ambient	833	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55 ~ +150	℃

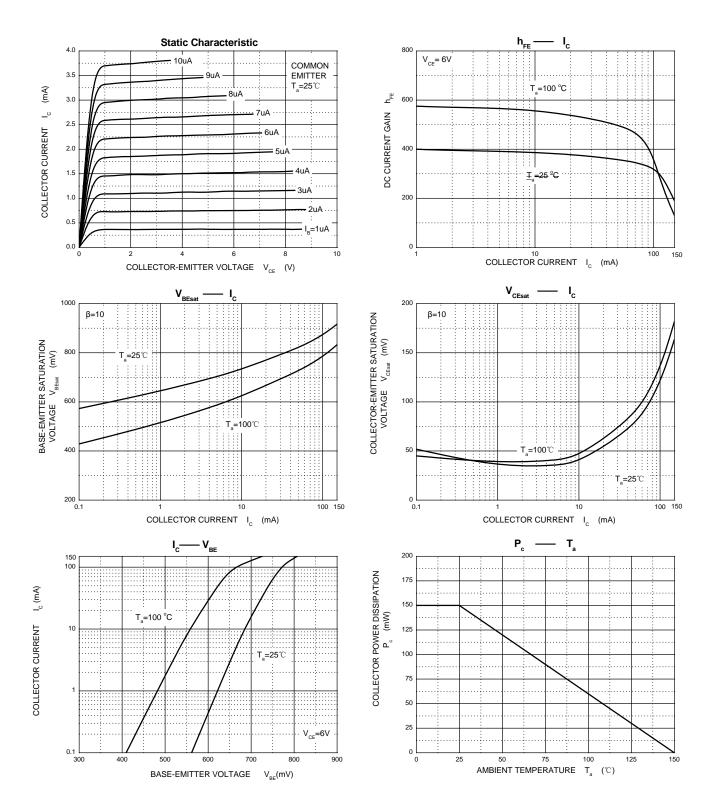
ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μΑ,I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 100μA, I _C =0	5			V
Collector cut-off current	Ісво	V _{CB} = 60V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} = 6V, I _C = 2mA	70		700	
Collector-emitter saturation voltage	V _{CE} (sat)	Ic=100mA, I _B = 10mA		0.1	0.25	V
base-emitter saturation voltage	V _{BE(sat)}	Ic=100mA, I _B = 10mA			1	V
Transition frequency	f⊤	V _{CE} =10V, I _C = 1mA	80			MHz
Collector output capacitance Cob		V _{CB} =10V,I _E =0,f=1MH _Z		2.0	3.5	pF
Noise figure NF		V_{CE} =6 V , I_{C} =0.1 m A, R g=10 k Ω, f =1 K H $_{Z}$		1.0	10	dB

CLASSIFICATION OF hFE

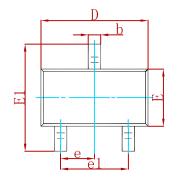
Rank	0	Y	GR	BL
Range	70-140	120-240	200-400	350-700
Marking	ALO	ALY	ALG	ALL

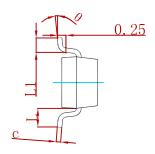


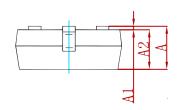




PACKAGE MECHANICAL DATA

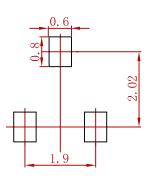






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layoue



- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.

REELSPECIFICATION

P/N	PKG	QTY
KTC3875-O	SOT-23	3000
KTC3875-Y	SOT-23	3000
KTC3875-GR	SOT-23	3000
KTC3875-BL	SOT-23	3000



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